# **CNZ1021** (ON1021), **CNZ1023** (ON1023), **CNA1009H** (ON1024)

#### Photo Interrupter

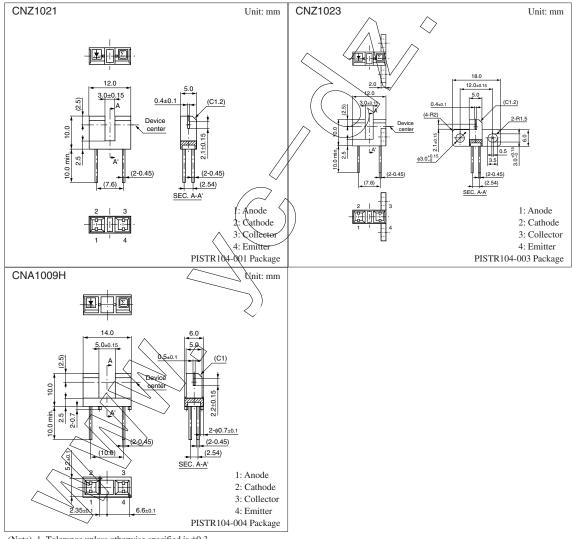
#### For contactless SW, object detection

#### Overview

CNZ1021, CNZ1023 and CNA1009H are a transmissive photosensor in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

#### Features

- Highly precise position detection: 0.25 mm
- Gap width: 3 mm (CNZ1021, CNZ1023)
  - 5 mm (CNA1009H)

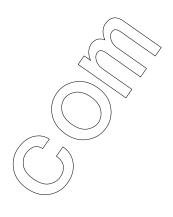


(Note) 1. Tolerance unless otherwise specified is ±0.3 2. ( ) Dimension is reference

Note) The part numbers in the parenthesis show conventional part number.

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Symbol	Rating	Unit		
Input (Light	Reverse	se CNZ1021		3	V
emitting diode)	voltage	CNZ1023		3	
		CNA1009H		5	
	Forward current		I <sub>F</sub>	50	mA
	Power dissipation *1		P <sub>D</sub>	75	mW
Output (Photo	Collector-emitter voltage		V <sub>CEO</sub>	30	V
transistor)	(Base open)				
	Emitter-collector voltage		V <sub>ECO</sub>	5	V
	(Base open)				
	Collector current		I <sub>C</sub>	20	mA
	Collector pow	er dissipation *2	P <sub>C</sub>	100	mW
Temperature	Operating ambient temperature		T <sub>opr</sub>	-25 to +85	°C
	Storage tem	perature	T <sub>stg</sub>	-40 to +100	°C



Note) \*1: Input power derating ratio is 1.0 mW/°C at  $T_a \ge 25$  °C.

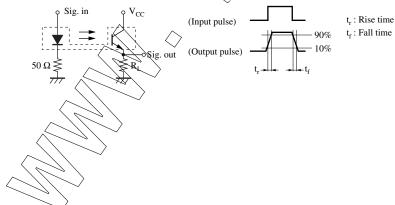
\*2: Output power derating ratio is 1.33 mW/°C at  $T_a \ge 25$  °C.

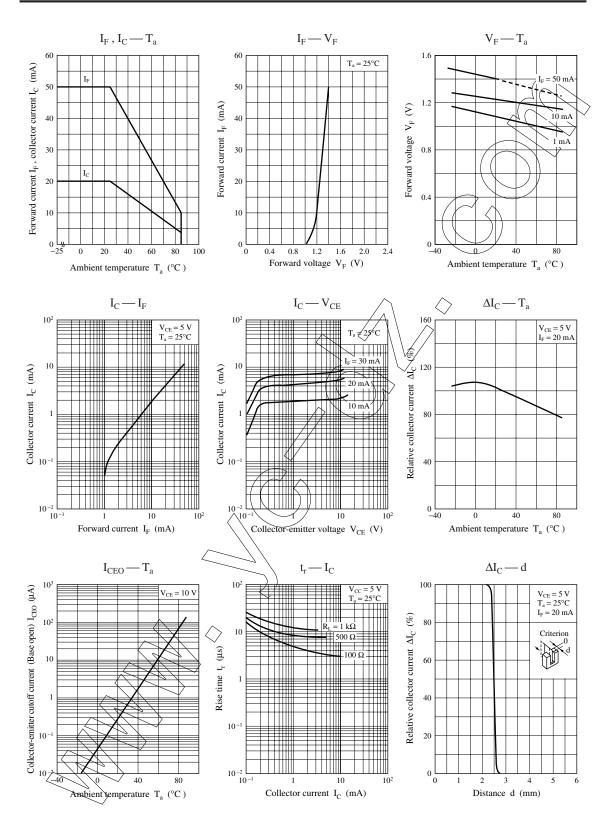
#### Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input	Forward voltage	V <sub>F</sub>	$I_F = 20 \text{ mA}$		1.25	1.40	V
characteristics	Reverse current	I <sub>R</sub>	$V_R = 3 V$			10	μΑ
Output	Collector-emitter cutoff current	I <sub>CEO</sub>	$V_{CE} = 10^{\circ}$ V		10	200	nA
characteristics	(Base open)		$\sim$				
Transfer characteristics	Collector current	I <sub>C</sub>	$V_{CC} = 5 V_{r} I_{F} = 20 \text{ mA}, R_{L} = 100 \Omega$	0.5		15.0	mA
	Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm F} = 40 \text{ mA}, I_{\rm C} = 1 \text{ mA}$			0.4	V
	Rise time *	t/	$V_{\rm CC} = 5 V A_{\rm C} = 1  \rm mA$		5		μs
	Fall time *	t <sub>f</sub>	$R_{\rm L} = 100 \ \Omega$		5		μs

Note) 1. Input and output are practiced by electricity.

- 2. This device is designed be disregarded radiation.
- 3. \*: Switching time measurement circuit





## A Caution for Safety

### A DANGER

#### This product contains Gallium Arsenide (GaAs).

GaAs powder and vapor are hazardous to human health if inhaled or ingested. Do not burn, destroy, cut, cleave off, or chemically dissolve the product. Follow related laws and ordinances for disposal. The product should be excluded form general industrial waste or household garbage.

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